

Thomas Frost

List of Publications by Year in descending order

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38
papers

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citations

623734

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39
all docs

39
docs citations

39
times ranked

1294
citing authors

#	ARTICLE	IF	CITATIONS
1	Room Temperature GaN-Based Edge-Emitting Spin-Polarized Light Emitting Diode. IEEE Photonics Technology Letters, 2017, 29, 338-341.	2.5	18
2	Room-Temperature Spin Polariton Diode Laser. Physical Review Letters, 2017, 119, 067701.	7.8	34
3	Red and Near-Infrared III-Nitride Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-9.	2.9	12
4	The role of defects in lowering the effective polariton temperature in electric and optically pumped polariton lasers. Applied Physics Letters, 2016, 108, 041102.	3.3	9
5	InGaN/GaN nanowire LEDs and lasers. , 2016, , .		2
6	Linearly and circularly polarized ultraviolet GaN microcavity polariton lasers. , 2016, , .		0
7	High performance red-emitting multiple layer InGaN/GaN quantum dot lasers. Japanese Journal of Applied Physics, 2016, 55, 032101.	1.5	30
8	Output polarization characteristics of a GaN microcavity diode polariton laser. Physical Review B, 2016, 94, .	3.2	13
9	Small-signal modulation characteristics of a polariton laser. Scientific Reports, 2015, 5, 11915.	3.3	8
10	0.5-1.3 μm III-nitride lasers and light emitting diodes epitaxially grown on (001) silicon. , 2015, , .		0
11	High performance InGaN/(In)GaN quantum dot ($\lambda = 630 \text{ nm}$) lasers. , 2015, , .		0
12	Physical model for indium-rich InGaN/GaN self-assembled quantum dot ridge-waveguide lasers emitting		0
13	Formation and Nature of InGaN Quantum Dots in GaN Nanowires. Nano Letters, 2015, 15, 1647-1653.	9.1	58
14	An enhanced surface passivation effect in InGaN/GaN disk-in-nanowire light emitting diodes for mitigating Shockley-Read-Hall recombination. Nanoscale, 2015, 7, 16658-16665.	5.6	84
15	Optical constants of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 0.73$) in the visible and near-infrared wavelength regimes. Optics Letters, 2015, 40, 3304.	3.3	9
16	Physical model for high indium content InGaN/GaN self-assembled quantum dot ridge-waveguide lasers emitting at red wavelengths ($\lambda \sim 630 \text{ nm}$). Optics Express, 2015, 23, 12850.	3.4	11
17	Small signal modulation characteristics of red-emitting ($\lambda = 610 \text{ nm}$) III-nitride nanowire array lasers on (001) silicon. Applied Physics Letters, 2015, 106, .	3.3	29
18	High-Speed Electrical Modulation of Polariton Lasers. , 2015, , .		0

#	ARTICLE	IF	CITATIONS
19	Room temperature electrically injected In _{0.4} Ga _{0.6} N/GaN quantum-dot visible (λ=620 nm) single photon source. , 2014, , .		0
20	Detailed model for the In _{0.18} Ga _{0.82} N/GaN self-assembled quantum dot active material for $\lambda = 420$ nm emission. Optics Express, 2014, 22, 22716.	3.4	8
21	GaAs-based high temperature electrically pumped polariton laser. Applied Physics Letters, 2014, 104, .	3.3	15
22	Electrically pumped single-photon emission at room temperature from a single InGaN/GaN quantum dot. Applied Physics Letters, 2014, 105, .	3.3	83
23	A monolithic InGaN/GaN disk-in-nanowire electrically pumped edge-emitting green (λ=533 nm) laser on (001) silicon. , 2014, , .		3
24	Monolithic Electrically Injected Nanowire Array Edge-Emitting Laser on (001) Silicon. Nano Letters, 2014, 14, 4535-4541.	9.1	177
25	Green-Emitting $(\lambda=525\text{--}600\text{ nm})$ InGaN/GaN Quantum Dot Light Emitting Diodes Grown on Quantum Dot Dislocation Filters. IEEE Journal of Quantum Electronics, 2014, 50, 228-235.	1.9	5
26	Temperature-dependent measurement of Auger recombination in In _{0.40} Ga _{0.60} N/GaN red-emitting ($\lambda=630\text{ nm}$) quantum dots. Applied Physics Letters, 2014, 104, 081121.	3.8	10
27	Room Temperature Electrically Injected Polariton Laser. Physical Review Letters, 2014, 112, 236802.	7.8	173
28	Room temperature strong coupling effects and polariton lasing under electrical injection. , 2014, , .		1
29	InGaN/GaN self-organized quantum dot lasers grown by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 566-570.	1.5	10
30	InGaN/GaN Quantum Dot Red $(\lambda=630\text{--}650\text{ nm})$ Laser. IEEE Journal of Quantum Electronics, 2013, 49, 923-931.	1.9	65
31	InGaN/GaN quantum dot lasers. , 2013, , .		0
32	Small-signal modulation and differential gain of red-emitting ($\lambda=630\text{ nm}$) InGaN/GaN quantum dot lasers. Applied Physics Letters, 2013, 103, .	3.3	17
33	Red-emitting InGaN/GaN quantum dot laser. , 2013, , .		2
34	Ridge waveguide InGaN/GaN quantum dot edge emitting visible lasers. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 816-819.	0.8	2
35	Monolithic integration of passive components with high performance quantum dot lasers. , 2012, , .		0
36	Continuous-wave operation and differential gain of InGaN/GaN quantum dot ridge waveguide lasers ($\lambda=420\text{ nm}$) on c-plane GaN substrate. Applied Physics Letters, 2012, 101, 041108.	3.3	30

#	ARTICLE	IF	CITATIONS
37	Characteristics of a high speed 1.22µm tunnel injection p-doped quantum dot excited state laser. Applied Physics Letters, 2011, 98, 011103.	3.3	15
38	High temperature stability in integrable quantum dot lasers with dry etched mirror facets for on-chip optical interconnects. , 2011, , .		0